Abstract

METHOD FOR RECLAIMING A SURFACE OF A SUBSTRATE

The invention relates to a method for reclaiming a surface of a substrate, wherein the surface, in particular a silicon surface, comprises a protruding residual topography, comprising at least the layer of a first material. By providing a filling material in the non-protruding areas of the surface of the substrate and the subsequent polishing, the reclaiming can be carried out such that the material consuming double-sided polishing step used in the prior art is no longer necessary.

Figure 2c